

F1G. 1

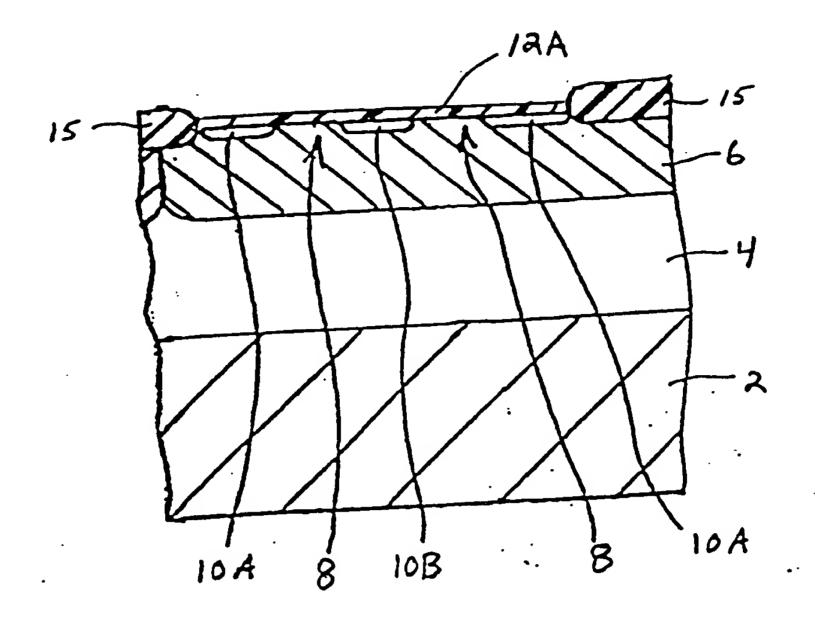
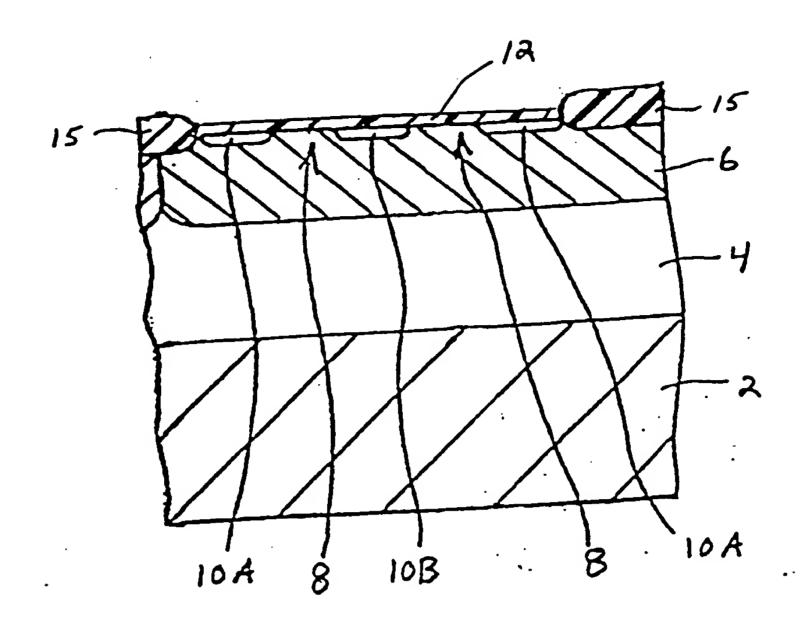
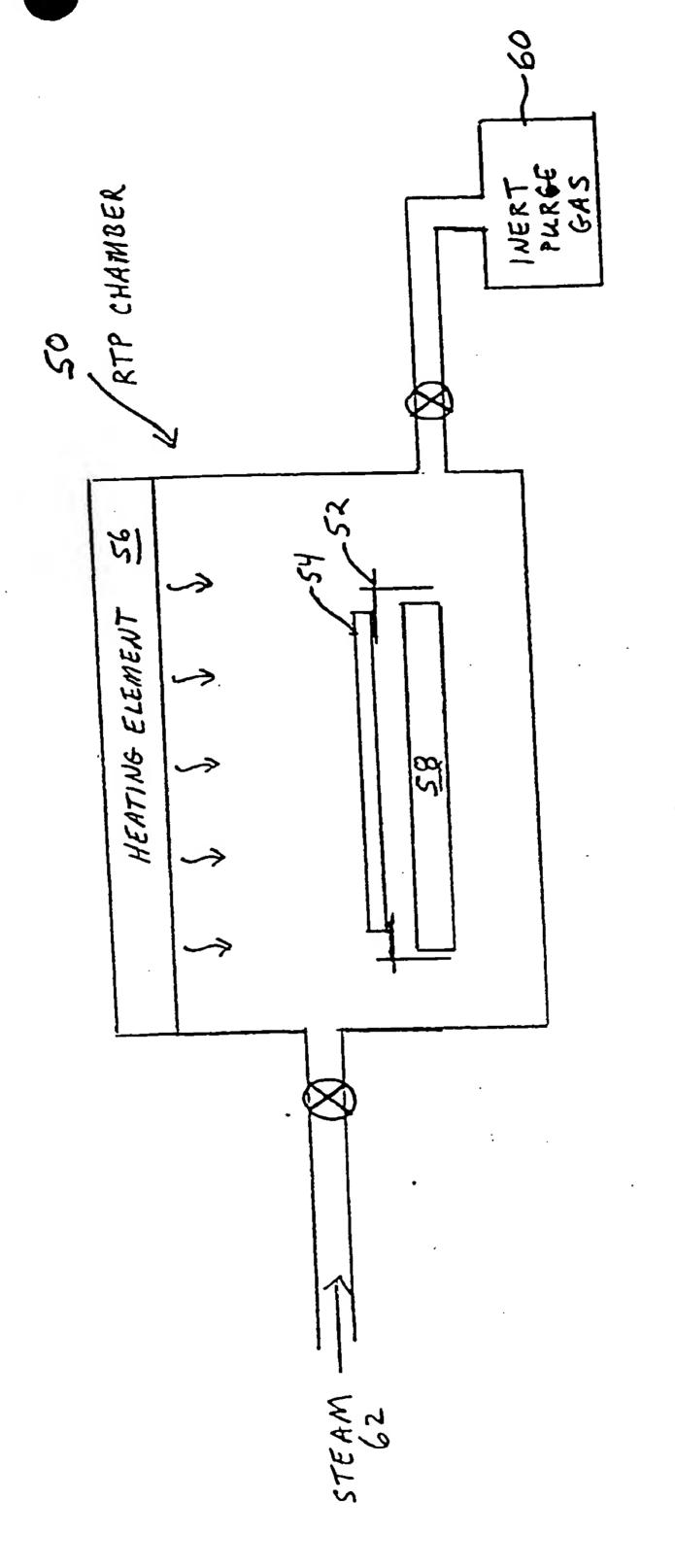


FIG. 2

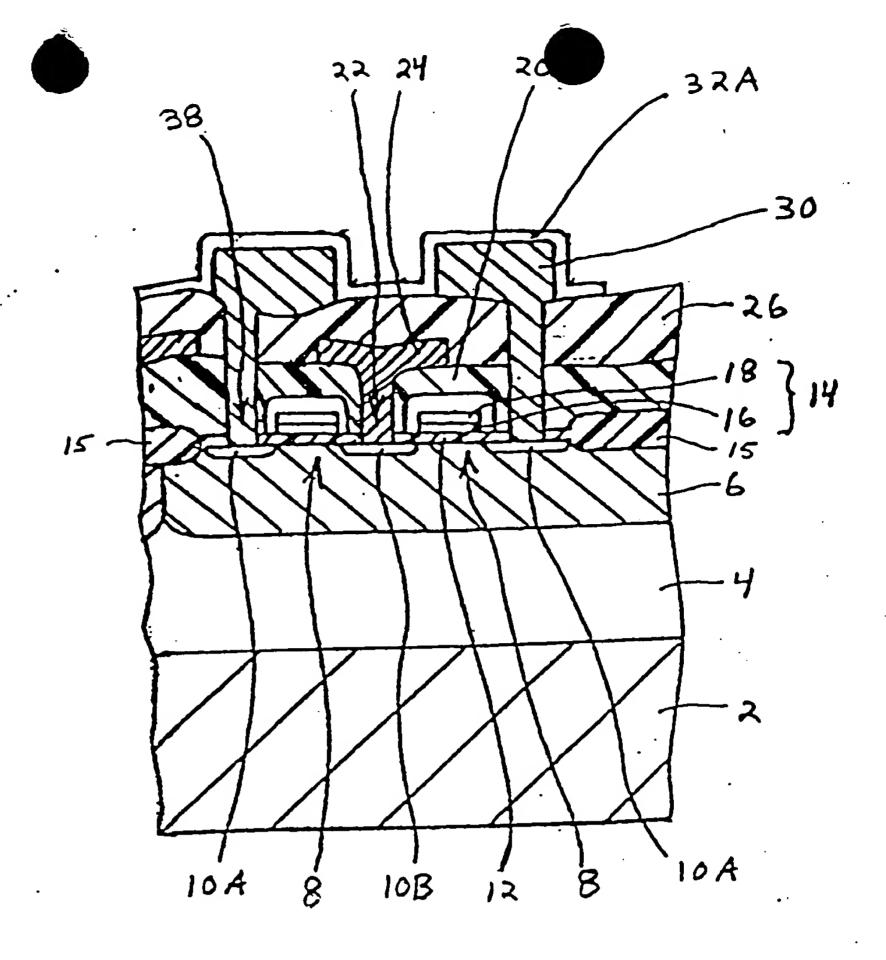


F1G. 3

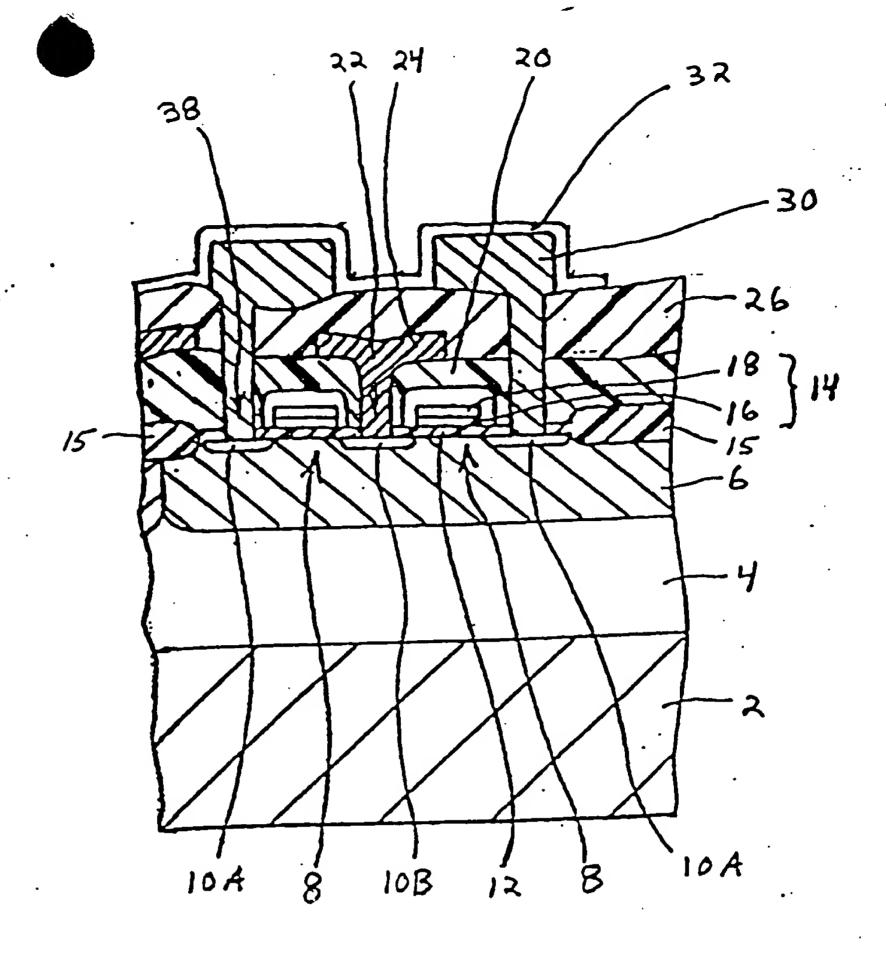
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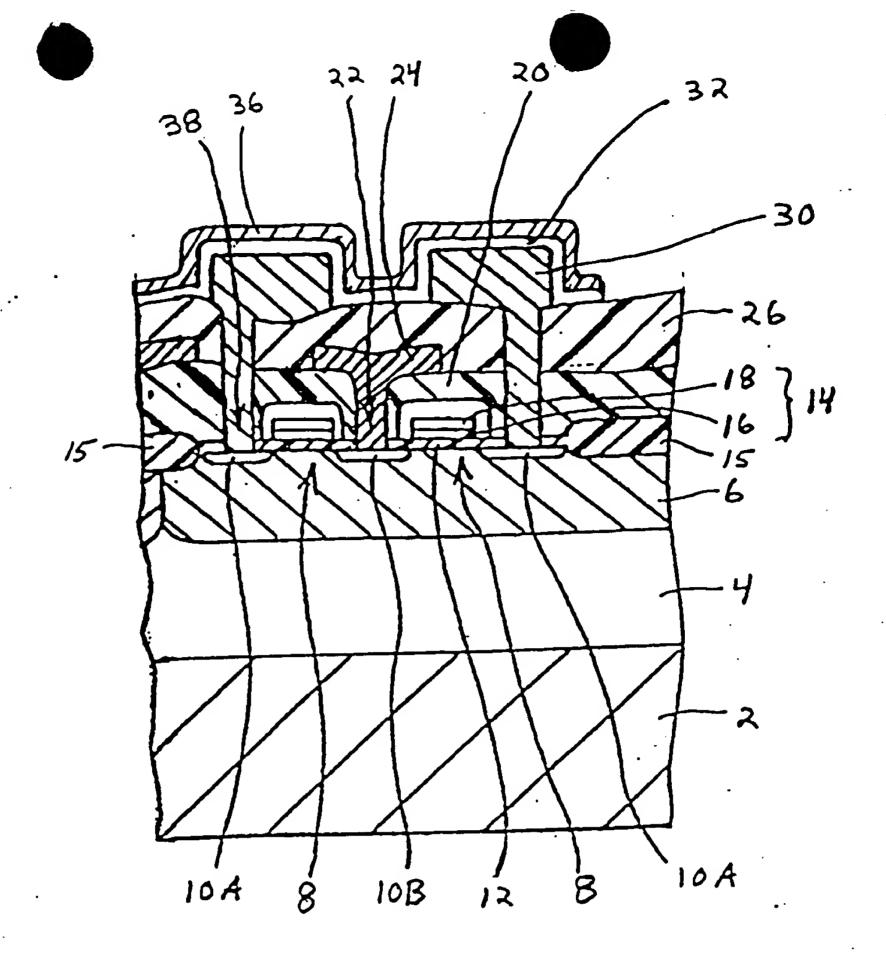
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F1G. 5



F1G. 6



F1G. 7

DEPOSIT DIELECTRIC OR INSULATING FILM

SUBJECT THE INSULATING FILM TO A HEAT TREATMENT IN AN AMBIENT COMPRISING A STABILIZING GAS INCLUDING A GAS SELECTED FROM THE GROUP CONSISTING OF N_2 , O_2 , O_3 , NO, OR N_2O_1

SUBJECT THE INSULATING FILM TO A WET OXIDATION IN A RAPID THERMAL PROCESS (RTP) CHAMBER

FIG. 8

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